

## RB551V-30 SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

### Features

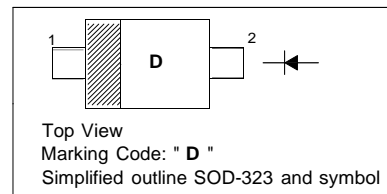
- Small surface mounting type
- Ultra low  $V_F$
- High reliability

### Applications

- High frequency rectification switching regulation

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	30	V
DC Reverse Voltage	$V_R$	20	V
Mean Rectifying Current	$I_O$	0.5	A
Peak Forward Surge Current (60 Hz for 1 Cyc.)	$I_{FSM}$	2	A
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 40 to + 125	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$ at $I_F = 500\text{ mA}$	$V_F$	0.36 0.47	V
Reverse Current at $V_R = 20\text{ V}$	$I_R$	100	$\mu\text{A}$

Note: ESD sensitive product handling required.

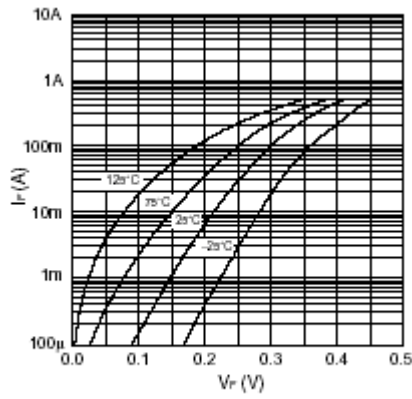


Fig.1 Forward characteristics

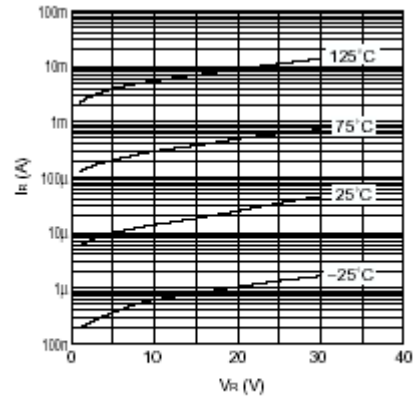


Fig.2 Reverse characteristics

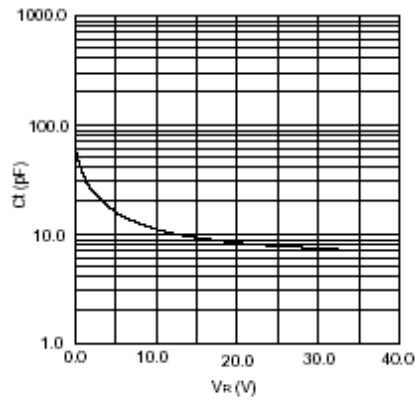


Fig.3 Capacitance between terminals characteristics

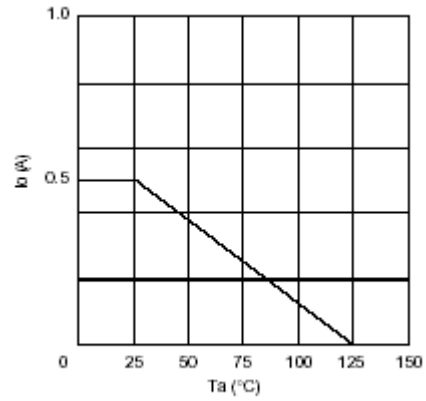


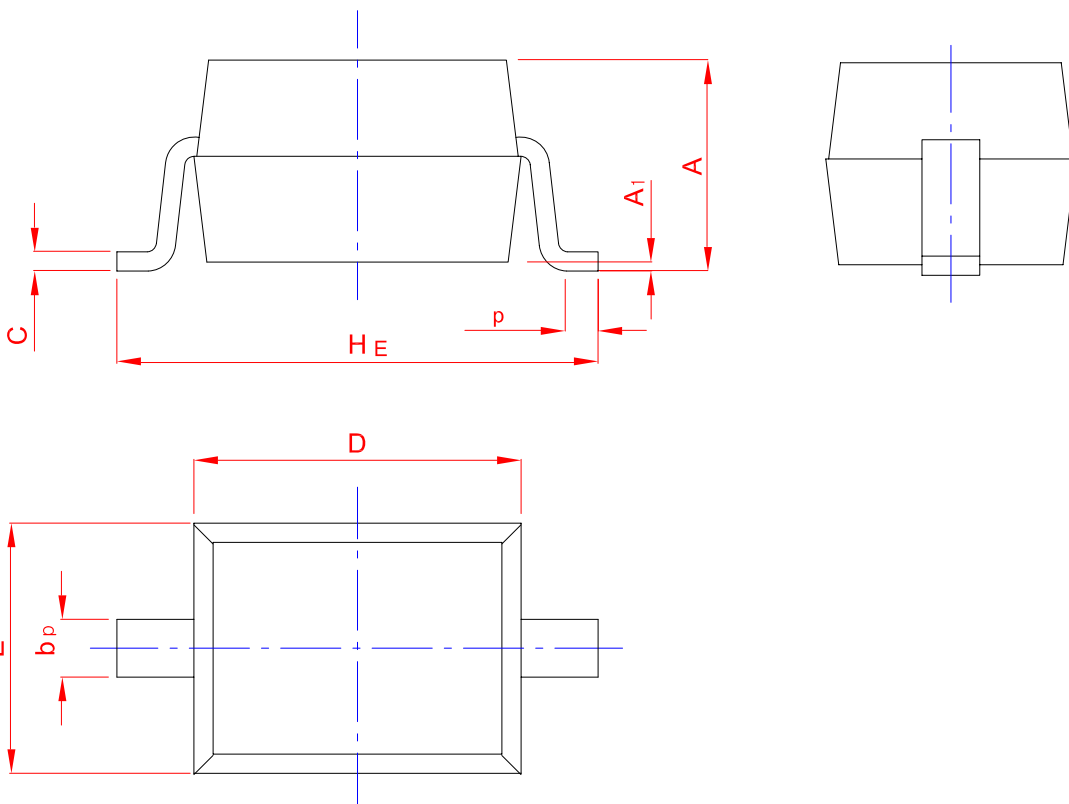
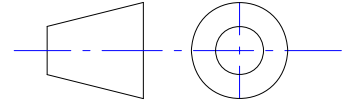
Fig.4 Derating curve



## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b <sub>p</sub>	C	D	E	H <sub>E</sub>	A <sub>1</sub>	L <sub>p</sub>
mm	1.20	0.40	0.15	1.80	1.35	2.80	0.10	0.50
	0.90	0.25	0.10	1.60	1.15	2.30	0.01	0.20